



InGaAs PIN Photodiode

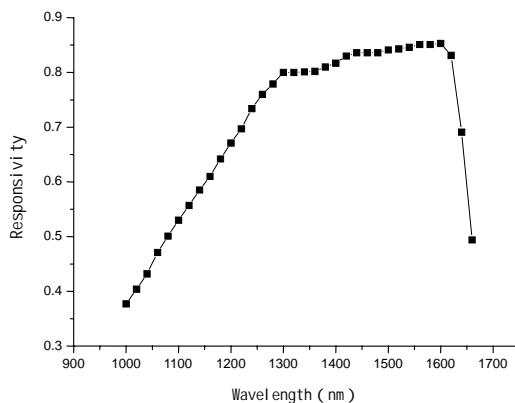
Type: PDS483-a

Electro-optical Characteristics(T=25):

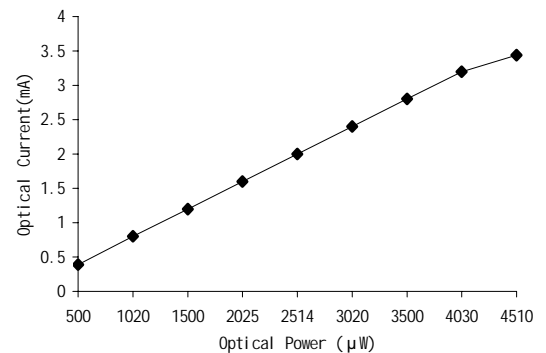
Parameters	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Wavelength			1000		1650	nm
Dark Current	I_D	$E_e=0, -5V$		2	5	nA
Responsivity(Unattenuation)	R_e	1310nm	0.85	0.90		A/W
Active diameter				1000		μm
Operating Voltage	V_{opr}			-1	-5	V

Absolute maximum ratings:

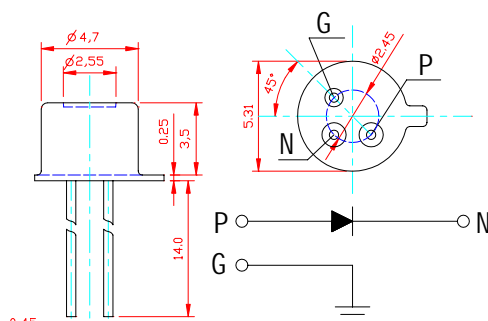
Parameters	Symbol	Value	Unit
Reverse Voltage	V_R	15	V
Reverse Current		5	mA
Forward Current	I_P	10	mA
Operating Temperature Range	T_{opr}	-40—+85	
Storage Temperature Range	T_{stg}	-40—+85	
Lead Solder Temperature		260	



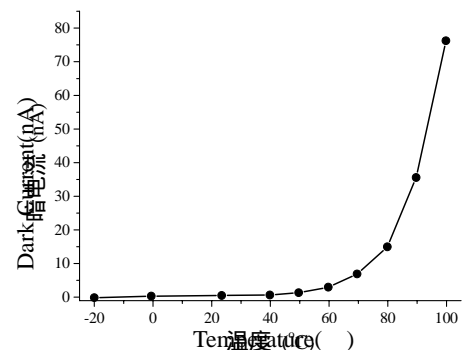
Spectrum Curve



Current-Optical Power Curve



Package Dimensions (mm)



Dark Current-Temperature Curve

Features: The large active area chip of the InGaAs photodiode guarantees the testing coincidence.

Precautions: ESD protection is imperative.